Influence of the Gate Leakage Current on the Noise Performance of MESFETs and MODFETs

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In this paper, the influence of the gate leakage current on the noise performance of MESFETs and MODFETs is investigated. It is shown that the noise performance of FETs is strongly dependent on the gate leakage current value, especially at a few GHz. The theoretical results are discussed and are compared with experimental data.

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